

# Epitaxial-Base, Silicon N-P-N and P-N-P VERSAWATT Transistors

General-Purpose Medium-Power Types for Switching and Amplifier Applications

**Features:**

- Low saturation voltages
- Complementary n-p-n and p-n-p types
- Maximum safe-area-of-operation curves specified for dc operation

The 2N6106-2N6111, 2N6288-2N6293, and 2N6473-2N6476 are epitaxial-base silicon transistors supplied in a VERSAWATT package. The 2N6288-2N6293, 2N6473, and 2N6474\* are n-p-n complements of p-n-p types 2N6106-2N6111, 2N6475, and 2N6476<sup>‡</sup>, respectively. All these transistors are intended for a wide variety of medium-power switching and amplifier applications, such as series and shunt regulators and driver and output stages of high-fidelity amplifiers.

The 2N6289, 2N6291, and 2N6293 p-n-p types and 2N6106, 2N6108, and 2N6110 p-n-p devices fit into TO-213AA sockets. The remaining types are supplied in the JEDEC TO-220AB straight-lead version of the VERSAWATT package. All of these devices are also available on special order in a variety of lead-form configurations.

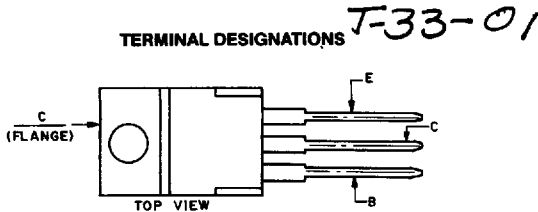
\*Formerly RCA Dev. Nos. TA7784, TA8323, TA7783, TA8232, TA7782, TA8231, TA8444, and TA8723, respectively.

‡Formerly RCA Dev. Nos. TA8210, TA7741, TA8211, TA7742, TA8212, TA7743, TA8445, and TA8722, respectively.

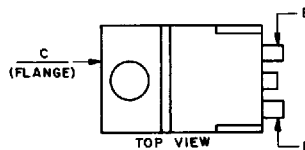
**MAXIMUM RATINGS, Absolute-Maximum Values:**

	2N6288		2N6290		2N6292		2N6473	2N6474
	N-P-N	2N6289	2N6291	2N6293	2N6475	2N6476 <sup>‡</sup>		
	P-N-P		2N6110 <sup>‡</sup>	2N6108 <sup>‡</sup>	2N6106 <sup>‡</sup>	2N6475 <sup>‡</sup>	2N6476 <sup>‡</sup>	
		2N6111 <sup>‡</sup>	2N6109 <sup>‡</sup>	2N6107 <sup>‡</sup>				
* V <sub>CEO</sub> .....	40	60	80	110	130		V	
* V <sub>CES</sub> (sus) R <sub>θJ</sub> = 100 Ω, V <sub>BE</sub> = 0 V .....	40	60	80	110	130		V	
V <sub>CEO</sub> (sus) .....	30	50	70	100	120		V	
* V <sub>ESD</sub> .....			5				V	
* I <sub>C</sub> (T <sub>C</sub> ≤ 106°C) .....			7		4		A	
* I <sub>B</sub> (T <sub>C</sub> ≤ 130°C) .....			3		2		A	
P <sub>T</sub>								
* T <sub>C</sub> ≤ 25°C .....			40				W	
T <sub>C</sub> > 25°C ≤ 100°C .....			16				W	
T <sub>C</sub> > 25°C .....			Derate linearly 0.32				W/°C	
T <sub>A</sub> ≤ 25°C .....			1.8				W	
T <sub>A</sub> > 25°C .....			Derate linearly 0.0144				W/°C	
* T <sub>stg</sub> , T <sub>J</sub> .....			-65 to 150				°C	
* T <sub>L</sub> At distances ≥ 1/8 in. (3.17 mm) from case for 10 s max. ....			235				°C	

\*In accordance with JEDEC registration data.



JEDEC TO-220AB



JEDEC TO-220AA

POWER TRANSISTORS

ELECTRICAL CHARACTERISTICS At Case Temperature ( $T_C$ ) = 25°C Unless Otherwise Specified

CHARACTERISTIC	TEST CONDITIONS <sup>†</sup>				LIMITS						UNITS
	VOLTAGE V dc		CURRENT A dc		2N6292 2N6293 2N6106 <sup>‡</sup> 2N6107 <sup>‡</sup>		2N6290 2N6291 2N6108 <sup>‡</sup> 2N6109 <sup>‡</sup>		2N6288 2N6289 2N6110 <sup>‡</sup> 2N6111 <sup>‡</sup>		
	V <sub>CE</sub>	V <sub>BE</sub>	I <sub>C</sub>	I <sub>B</sub>	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
I <sub>CER</sub> (R <sub>BE</sub> = 100 Ω)	75				-	0.1	-	-	-	-	mA
	55				-	-	-	0.1	-	-	
	35				-	-	-	-	-	0.1	
(R <sub>BE</sub> = 100 Ω, T <sub>C</sub> = 150°C)	70				-	2	-	-	-	-	mA
	50				-	-	-	2	-	-	
	30				-	-	-	-	-	2	
* I <sub>CEX</sub> (R <sub>BE</sub> = 100 Ω)	75	-1.5			-	0.1	-	-	-	-	mA
	56	-1.5			-	-	-	0.1	-	-	
	37.5	-1.5			-	-	-	-	-	0.1	
(R <sub>BE</sub> = 100 Ω, T <sub>C</sub> = 150°C)	70	-1.5			-	2	-	-	-	-	mA
	50	-1.5			-	-	-	2	-	-	
	30	-1.5			-	-	-	-	-	2	
* I <sub>CEO</sub>	60			0	-	1	-	-	-	-	mA
	40			0	-	-	-	1	-	-	
	20			0	-	-	-	-	-	1	
* I <sub>EBO</sub>		-5	0		-	1	-	1	-	1	
* V <sub>CEO(sus)</sub> <sup>b</sup>			0.1 <sup>a</sup>	0	70	-	50	-	30	-	V
* V <sub>CER(sus)</sub> <sup>b</sup> (R <sub>BE</sub> = 100 Ω)			0.1 <sup>a</sup>		80	-	60	-	40	-	V
* h <sub>FE</sub>	4		2 <sup>a</sup>		30	150	-	-	-	-	V
	4		2.5 <sup>a</sup>		-	-	30	150	-	-	
	4		3 <sup>a</sup>		-	-	-	-	30	150	
	4		7 <sup>a</sup>		2.3	-	2.3	-	2.3	-	
* V <sub>BE</sub>	4		2 <sup>a</sup>		-	1.5	-	-	-	-	V
	4		2.5 <sup>a</sup>		-	-	-	1.5	-	-	
	4		3 <sup>a</sup>		-	-	-	-	-	1.5	
	4		7 <sup>a</sup>		-	3	-	3	-	3	
* V <sub>CE(sat)</sub>			2 <sup>a</sup>	0.2	-	1	-	-	-	-	V
			2.5 <sup>a</sup>	0.25	-	-	-	1	-	-	
			3 <sup>a</sup>	0.3	-	-	-	-	-	1	
			7 <sup>a</sup>	3	-	3.5	-	3.5	-	3.5	
*  h <sub>fe</sub>   (f = 1 MHz) 2N6288-93	4		0.5		4	-	4	-	4	-	MHz
	2N6106-11	-4	-0.5		10	-	10	-	10	-	
* h <sub>fe</sub> (f = 50 kHz)	4		0.5		20	-	20	-	20	-	
* f <sub>T</sub> 2N6288-93	4		0.5		10	-	10	-	10	-	MHz
	2N6106-11	-4	-0.5		10	-	10	-	10	-	
* C <sub>obo</sub> (f = 1 MHz)	10 <sup>c</sup>		0		-	250	-	250	-	250	pF
R <sub>θJC</sub>					-	3.125	-	3.125	-	3.125	°C/W
R <sub>θJA</sub>					-	70	-	70	-	70	°C/W

<sup>†</sup> In accordance with JEDEC registration data.

<sup>a</sup> Pulsed: Pulse duration = 300 μs, duty factor = 0.018.

<sup>b</sup> CAUTION: The sustaining voltage V<sub>CEO(sus)</sub> and V<sub>CER(sus)</sub> MUST NOT be measured on a curve tracer.

<sup>c</sup> V<sub>CEB</sub> value.

<sup>‡</sup> For p-n-p devices, voltage and current values are negative.

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2N6106-2N6111, 2N6288-2N6293, 2N6473-2N6476

ELECTRICAL CHARACTERISTICS At Case Temperature ( $T_C$ ) = 25°C Unless Otherwise Specified

CHARACTERISTIC	TEST CONDITIONS				LIMITS				UNITS
	VOLTAGE V dc		CURRENT A dc		2N6474 2N6476*		2N6473 2N6475*		
	V <sub>CE</sub>	V <sub>BE</sub>	I <sub>C</sub>	I <sub>B</sub>	Min.	Max.	Min.	Max.	
I <sub>CER</sub> (R <sub>BE</sub> = 100 Ω)	120				–	0.1	–	–	mA
	100				–	–	–	0.1	
(R <sub>BE</sub> = 100 Ω T <sub>C</sub> = 100°C)	120				–	2	–	–	mA
	100				–	–	–	2	
* I <sub>CEX</sub> (R <sub>BE</sub> = 100 Ω)	120	–1.5			–	0.1	–	–	mA
	100	–1.5			–	–	–	0.1	
(R <sub>BE</sub> = 100 Ω, T <sub>C</sub> = 100°C)	120	–1.5			–	2	–	–	mA
	100	–1.5			–	–	–	2	
* I <sub>CEO</sub>	60			0	–	1	–	–	mA
	50			0	–	–	–	1	
* I <sub>EBO</sub>		–5		0	–	1	–	1	mA
* V <sub>CEO(sus)</sub> <sup>b</sup>			0.1 <sup>a</sup>	0	120	–	100	–	
V <sub>CE(sus)</sub> <sup>b</sup> (R <sub>BE</sub> = 100 Ω)			0.1 <sup>a</sup>		130	–	110	–	V
* h <sub>FE</sub>	4		1.5 <sup>a</sup>		15	150	15	150	V
	2.5		4 <sup>a</sup>		2	–	2	–	
* V <sub>BE</sub>	4		1.5 <sup>a</sup>		–	2	–	2	V
	2.5		4 <sup>a</sup>		–	3.5	–	3.5	
* V <sub>CE(sat)</sub>			1.5 <sup>a</sup>	0.15	–	1.2	–	1.2	V
			4 <sup>a</sup>	2	–	2.5	–	2.5	
*  h <sub>fe</sub>   (f = 1 MHz)									V
2N6473-74	4		0.5		4	–	4	–	
2N6475-76	–4		–0.5		5	–	5	–	
* h <sub>fe</sub> (f = 50 kHz)	4		0.5		20	–	20	–	V
f <sub>T</sub>									
2N6473-74	4		0.5		4	–	4	–	MHz
2N6475-76	–4		–0.5		5	–	4	–	
* C <sub>obo</sub> (f = 1 MHz)	10 <sup>c</sup>		0		–	250	–	250	pF
R <sub>θJC</sub>					–	3.125	–	3.125	°C/W
R <sub>θJA</sub>					–	70	–	70	°C/W

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\* In accordance with JEDEC registration data

<sup>a</sup> Pulsed: Pulse duration = 300 μs, duty factor = 0.018.

<sup>b</sup> CAUTION: The sustaining voltage V<sub>CEO(sus)</sub> are V<sub>CE(sus)</sub> MUST NOT be measured on a curve tracer.

<sup>c</sup> V<sub>CB</sub> value.

♦ For p-n-p devices, voltage and current values are negative.

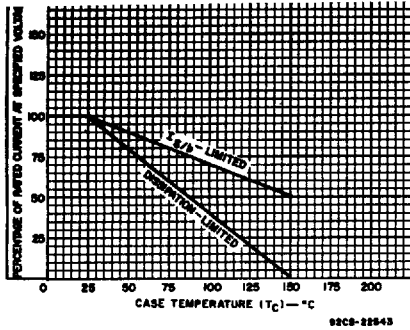


Fig. 1 - Current derating curves for all types.

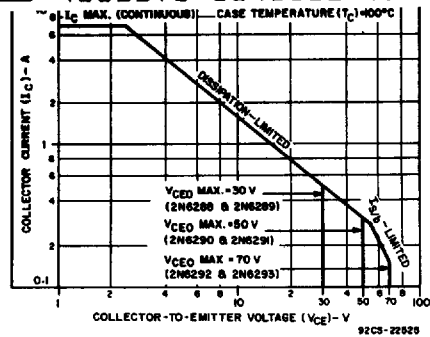


Fig. 2 - Maximum operating areas for 2N6288 - 2N6293 ( $T_C = 100^\circ C$ ).

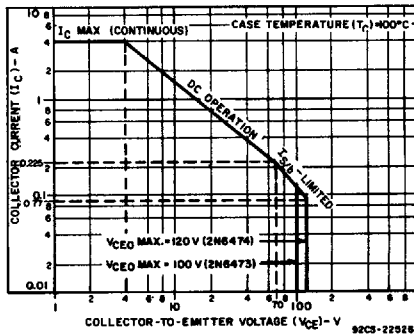


Fig. 3 - Maximum operating areas for 2N6473 - 2N6474 ( $T_C = 100^\circ C$ ).

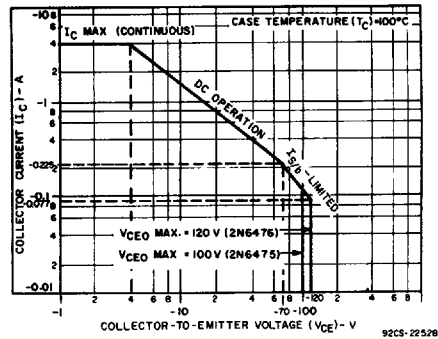


Fig. 4 - Maximum operating areas for 2N6475 and 2N6476 ( $T_C = 100^\circ C$ ).

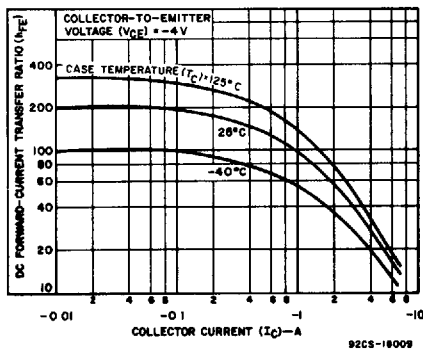


Fig. 5 - Typical dc beta characteristics for 2N6106 - 2N6111.

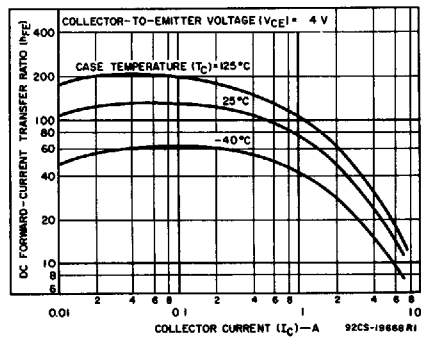


Fig. 6 - Typical dc beta characteristics for 2N6288 - 2N6293.

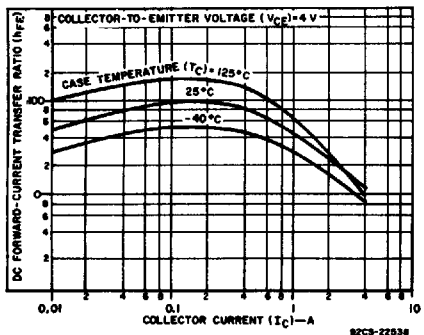


Fig. 7 - Typical dc beta characteristics for 2N6473 and 2N6474.

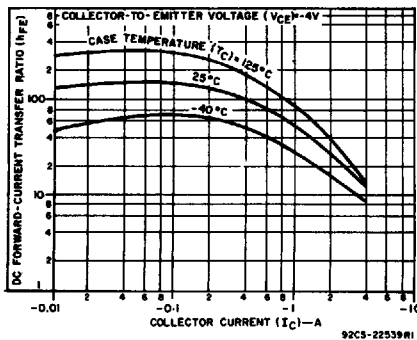


Fig. 8 - Typical dc beta characteristics for 2N6475 and 2N6476.

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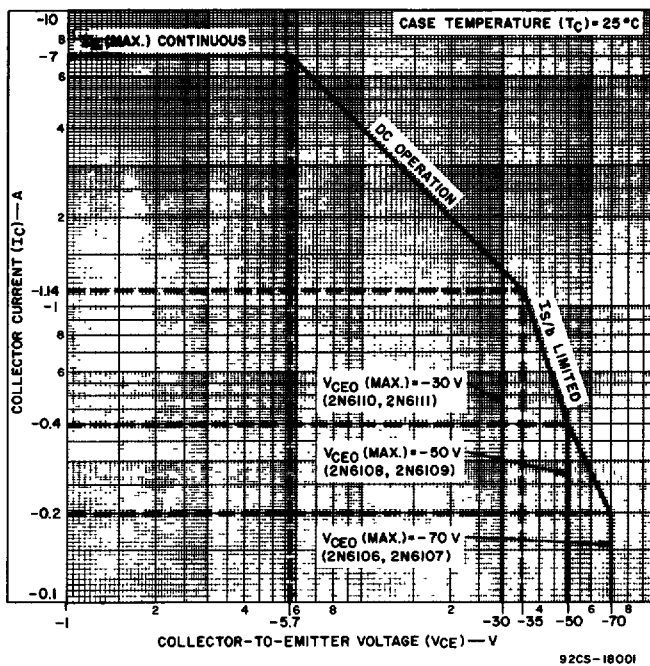


Fig. 9 - Maximum operating areas for 2N6106 - 2N6111 ( $T_C = 25^\circ C$ ).

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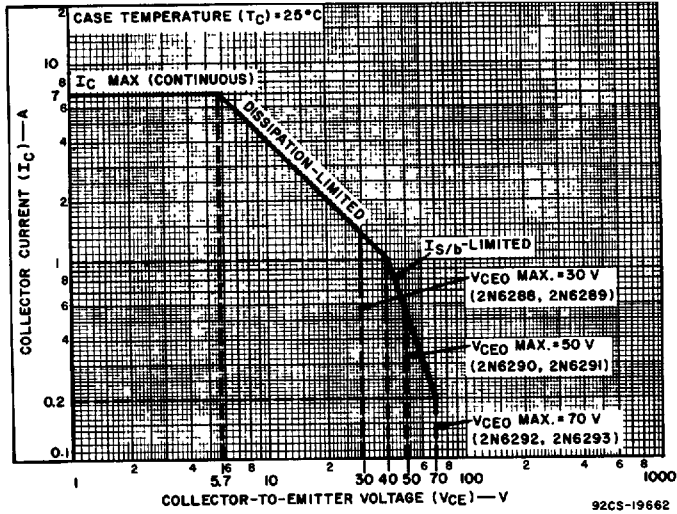


Fig. 10 - Maximum operating areas for 2N6288-2N6293 ( $T_C = 25^\circ C$ ).

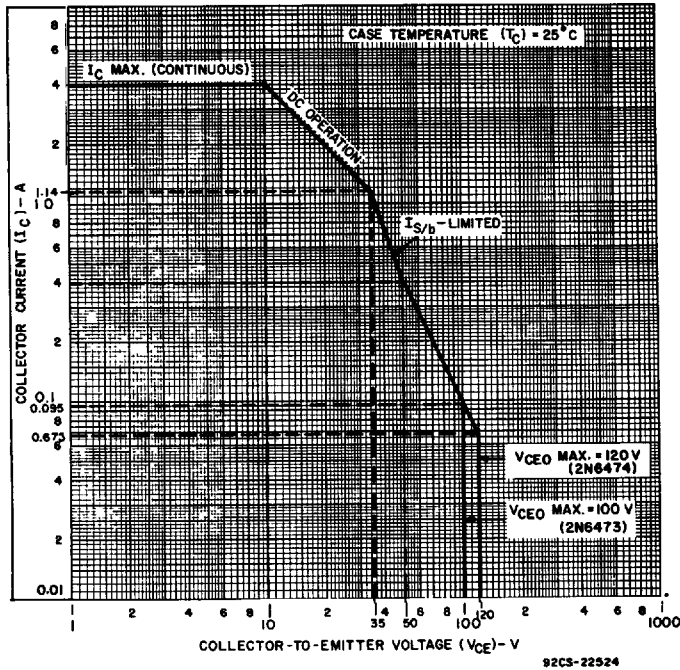


Fig. 11 - Maximum operating areas for 2N6473 and 2N6474 ( $T_C = 25^\circ C$ ).

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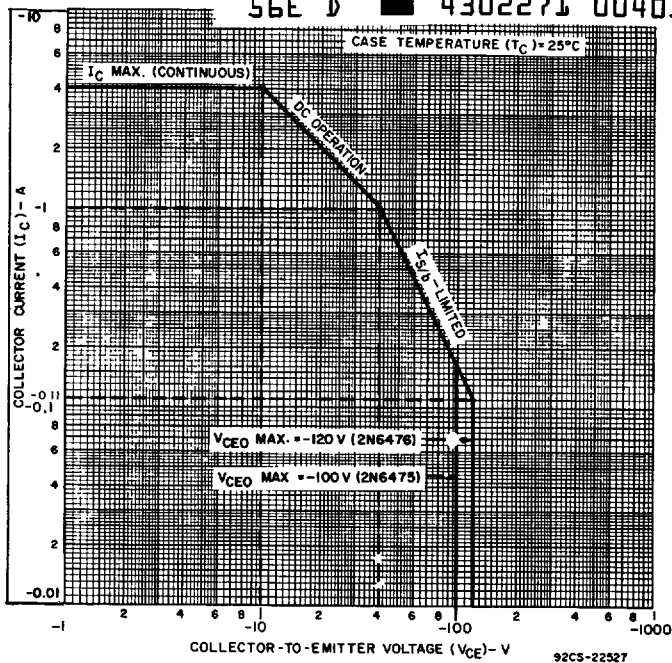


Fig. 12 - Maximum operating areas for 2N6475 - 2N6476 ( $T_C = 25^\circ C$ ).

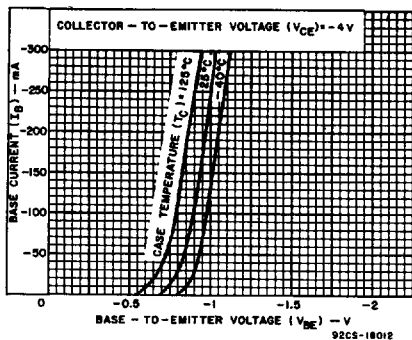


Fig. 13 - Typical input characteristics for 2N6106 - 2N6111, 2N6475, and 2N6476.

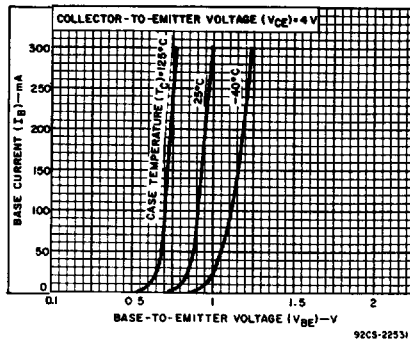


Fig. 14 - Typical input characteristics for 2N6288 - 2N6293.

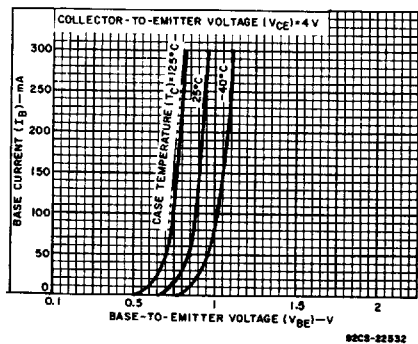


Fig. 15 - Typical input characteristics for 2N6473 - 2N6474.

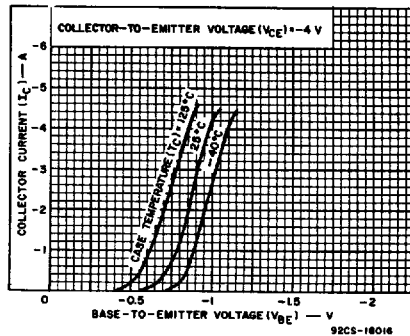


Fig. 16 - Typical transfer characteristics for 2N6106 - 2N6111.

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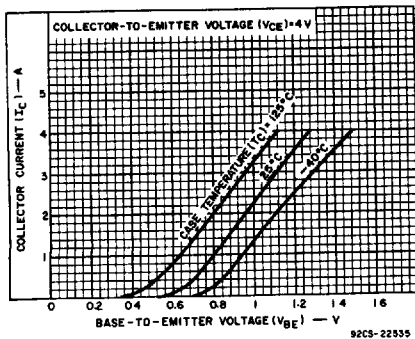


Fig. 17 - Typical transfer characteristics for 2N6288 - 2N6293.

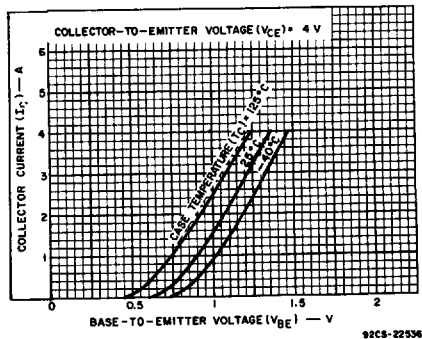


Fig. 18 - Typical transfer characteristics for 2N6473 and 2N6474.

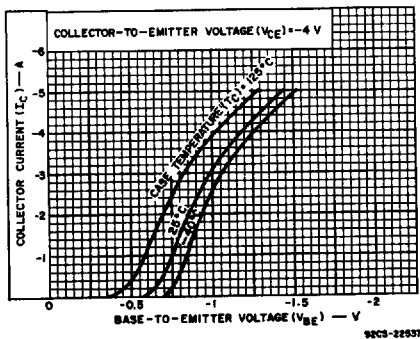


Fig. 19 - Typical transfer characteristics for 2N6475 and 2N6476.

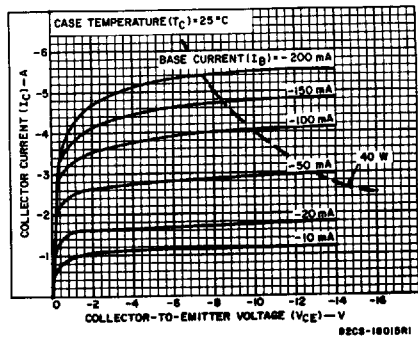


Fig. 20 - Typical output characteristics for 2N6106 - 2N6111.

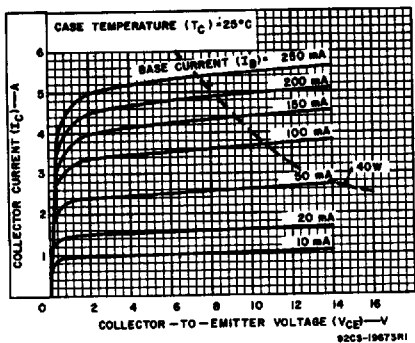


Fig. 21 - Typical output characteristics for 2N6288 - 2N6293.

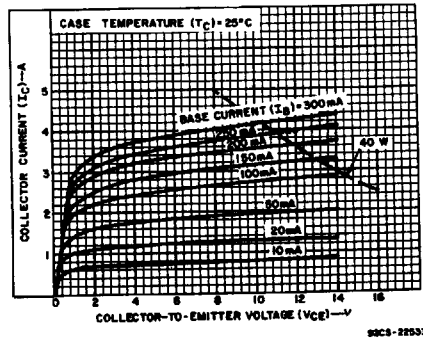


Fig. 22 - Typical output characteristics for 2N6473 and 2N6474.

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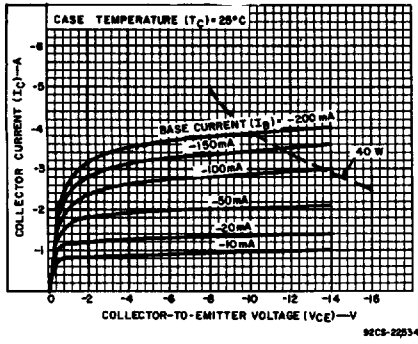


Fig. 23 - Typical output characteristics for 2N6475 and 2N6476.

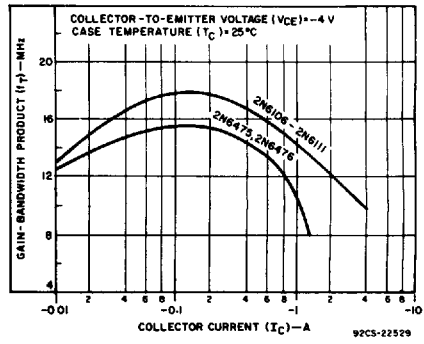


Fig. 24 - Typical gain-bandwidth product 2N6106 - 2N6111, 2N6475, and 2N6476.

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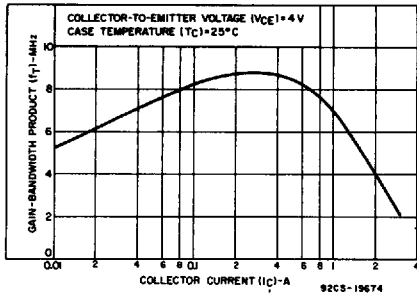


Fig. 25 - Typical gain-bandwidth product for 2N6288 - 2N6293.

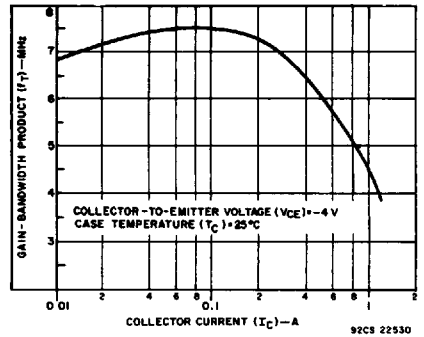


Fig. 26 - Typical gain-bandwidth product for 2N6473 and 2N6474.

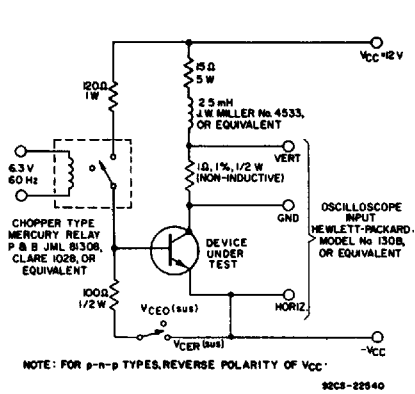


Fig. 27 - Circuit used to measure sustaining voltage  $V_{CE}(sus)$  for all types.

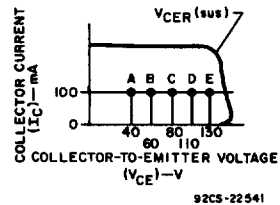


Fig. 28 - Oscilloscope delay for measurement of sustaining voltage (test circuit shown in Fig. 27).  
**Note:** Curve will be inverted and polarity reversed for p-n-p types. The sustaining voltage,  $V_{CE}(sus)$ , is acceptable when the traces fall to the right and above the designated points:  
 Point A: 2N6110, 2N6111, 2N6288, 2N6289  
 Point B: 2N6108, 2N6109, 2N6290, 2N6291  
 Point C: 2N6106, 2N6107, 2N6292, 2N6293  
 Point D: 2N6475, 2N6473  
 Point E: 2N6476, 2N6474

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